

SCCS025 - May 1993 - Revised March 2000

Dual 8-Bit Parity Generator/Checker

Features

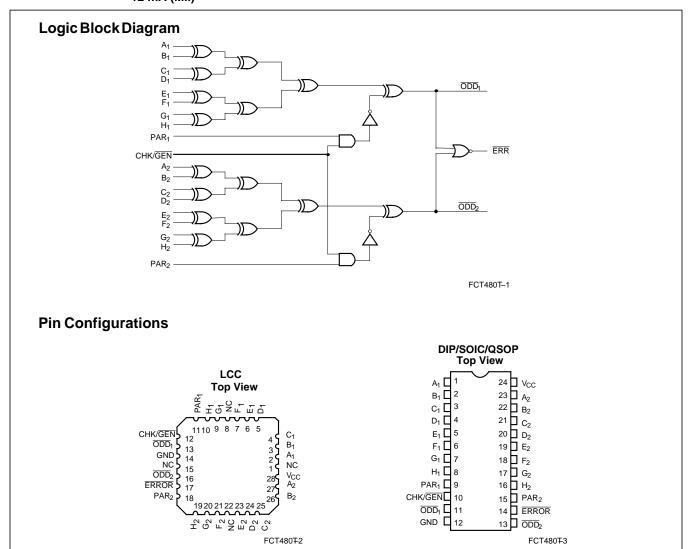
- Function, pinout and drive compatible with FCT and F logic
- FCT-A speed at 7.5 ns max. (Com'l) FCT-B speed at 5.6 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- · Power-off disable feature
- · Matched rise and fall times
- ESD > 2000V
- Fully compatible with TTL input and output logic levels
- Sink Current 64 mA (Com'l), 32 mA (Mil)
 - 32 mA (Mil)
 Source Current 32 mA (Com'l),
 12 mA (Mil)

- Two 8-bit parity generator/checkers
- Open drain Active LOW parity error output
- Expandable for larger word widths

Functional Description

The FCT480T is a high-speed dual 8-bit parity generator/checker. Each parity generator/checker accepts eight data bits and one parity bit as inputs, and generates a sum and parity error output. The FCT480T can be used in ODD parity systems. The parity error output is open-drain, designed for easy expansion of the word width by a wired-OR connection of several FCT480T type devices. Since additional logic is not needed, the parity generation or checking times remain the same as for an individual FCT480T device.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.





Function Table

Inputs					Outputs			
A ₁ to H ₁	A ₂ to H ₂	CHK/GEN	PAR ₁	PAR ₂	ODD ₁	ODD ₂	ERROR	
Number of A ₁ to H ₁ Inputs	Number of A ₂ to H ₂ Inputs	Н	Н	Н	L	L	Н	
HIGH is EVEN	HIGH is EVEN		L	Н	Н	L	L	
			Н	L	L	Н	L	
			L	L	Н	Н	L	
		L	Х	Х	Н	Н	L	
	Number of Inputs HIGH A ₂	Н	Н	Н	L	Н	L	
	to H ₂ is ODD		L	Н	Н	Н	L	
			Н	L	L	L	Н	
			L	L	Н	L	L	
		L	Х	Х	Н	L	L	
Number of A ₁ to H ₁ Inputs	Number of A ₂ to H ₂ Inputs HIGH is EVEN	Н	Н	Н	Н	L	L	
HIGH is ODD		HIGH IS EVEN		L	Н	L	L	Н
			Н	L	Н	Н	L	
			L	L	L	Н	L	
		L	Х	Х	L	Н	L	
	Number of A ₂ to H ₂ Inputs HIGH is ODD	ıts H	Н	Н	Н	Н	L	
			L	Н	L	Н	L	
			Н	L	Н	L	L	
			L	L	L	L	Н	
		L	Х	Х	L	L	Н	

Maximum Ratings^[1, 2]

(Above which the useful life may be impaired. For user guidelines, not tested.)

·
Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied65°C to +135°C
Supply Voltage to Ground Potential0.5V to +7.0V
DC Input Voltage0.5V to +7.0V
DC Output Voltage0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin)120 mA
Power Dissipation

Static Discharge Voltage.....>2001V (per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	v _{cc}
Commercial	All	–40°C to +85°C	5V ± 5%
Military ^[3]	All	–55°C to +125°C	5V ± 10%

Notes:

- 1. Unless otherwise noted, these limits are over the operating free-air tem-
- Offices of the Wise Tribled, these fiffiles are over the operating free-air terreperature range.
 Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
 T_A is the "instant on" case temperature.



Electrical Characteristics Over the Operating Range

Parameter	Description	Test Condition	Min.	Typ. ^[4]	Max.	Unit	
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -32 mA Com'I		2.0			V
		V _{CC} = Min., I _{OH} = -15 mA	Com'l	2.4	3.3		V
		V _{CC} = Min., I _{OH} = -12 mA	Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 64 mA	Com'l		0.3	0.55	V
		V _{CC} = Min., I _{OL} = 32 mA	Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage			2.0			V
V _{IL}	Input LOW Voltage					0.8	V
V _H	Hysteresis ^[5]	All inputs			0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} = Min., I _{IN} = -18 mA			-0.7	-1.2	V
I _I	Input HIGH Current	$V_{CC} = Max., V_{IN} = V_{CC}$				5	μΑ
I _{IH}	Input HIGH Current	$V_{CC} = Max., V_{IN} = 2.7V$				±1	μΑ
I _{IL}	Input LOW Current	$V_{CC} = Max., V_{IN} = 0.5V$	$V_{CC} = Max., V_{IN} = 0.5V$			±1	μΑ
I _{OZH}	Off State HIGH-Level Output Current	V _{CC} = Max., V _{OUT} = 2.7V				10	μΑ
I _{OZL}	Off State LOW-Level Output Current	$V_{CC} = Max., V_{OUT} = 0.5V$				-10	μΑ
Ios	Output Short Circuit Current ^[6]	$V_{CC} = Max., V_{OUT} = 0.0V$		-60	-120	-225	mA
I _{OFF}	Power-Off Disable	V _{CC} = 0V, V _{OUT} = 4.5V				±1	μΑ

Capacitance^[5]

Parameter	Description	Typ. ^[4]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Notes:

Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.

This parameter is specified but not tested.

Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.



Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[4]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V_{CC} =Max., $V_{IN} \le 0.2V$, $V_{IN} \ge V_{CC}$ -0.2V	0.1	0.2	mA
Δl _{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	V _{CC} =Max., V _{IN} =3.4V, ^[7] f ₁ =0, Outputs Open	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[8]	V_{CC} =Max., One Bit Toggling, 50% Duty Cycle, Outputs Open, $V_{IN} \le 0.2V$ or $V_{IN} \ge V_{CC}$ -0.2V	0.06	0.12	mA/ MHz
I _C	Total Power Supply Current ^[9]	V_{CC} =Max., 50% Duty Cycle, Outputs Open, One Bit Toggling at f_1 =2.5 MHz, $V_{IN} \le 0.2 V$ or $V_{IN} \ge V_{CC}$ -0.2V	0.7	1.4	mA
		V _{CC} =Max., 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =2.5 MHz, V _{IN} =3.4V or V _{IN} =GND	1.0	2.4	mA
		$V_{CC}=Max.$, 50% Duty Cycle, Outputs Open, Sixteen Bits Toggling at $f_1=2.5$ MHz, $V_{IN} \le 0.2V$ or $V_{IN} \ge V_{CC}=0.2V$	2.5	5.0 ^[10]	mA
		V _{CC} =Max., 50% Duty Cycle, Outputs Open, Sixteen Bits Toggling at f ₁ =2.5 MHz, V _{IN} =3.4V or V _{IN} =GND	6.5	21.0 ^[10]	mA

Switching Characteristics Over the Operating Range

		FCT480AT	FCT480BT		
	Description	Com'l	Military	Com'l	Unit
t _{PLH}	Propagation Delay	7.5	7.0	5.6	ns
t _{PHL}	A to EVEN/ODD	7.0	6.6	5.6	
t _{PLH} ^[11]	Propagation Delay	7.0	7.0	5.6	ns
t _{PHL}	A to ERROR	8.5	8.1	6.5	
t _{PLH}	Propagation Delay	6.5	6.3	5.9	ns
t _{PHL}	CHK/GEN to EVEN/ODD	7.5	7.4	5.9	
t _{PLH} ^[11]	Propagation Delay	7.5	7.1	5.7	ns
t _{PHL}	CHK/GEN to ERROR	7.0	6.9	5.5	

Notes:

- 7. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.

 8. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

 9. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
 I_C = I_{CC}+ΔI_{CC}D_HN_T+I_{CCD}(f₀/2 + f₁N₁)
 I_{CC} = Quiescent Current with CMOS input levels

 ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
 D_H = Duty Cycle for TTL inputs HIGH
 N_T = Number of TTL inputs at D_H
 I_{CC} = Dynamic Current caused by an input transition pair (HI H or I HI)
- - I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)
- f₀ = Clock frequency for registered devices, otherwise zero
 f₁ = Input signal frequency
 N₁ = Number of inputs changing at f₁
 All currents are in milliamps and all frequencies are in megahertz.

 10. Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.
- 11. t_{PLH} is measured up to $V_{OUT}=V_{OL}+0.3V$



Ordering Information

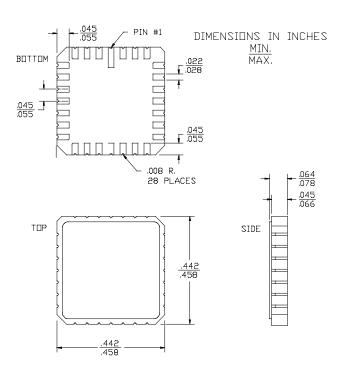
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
5.6	CY74FCT480BTPC	P13/13A	24-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT480BTQCT	Q13	24-Lead (150-Mil) QSOP	
	CY74FCT480BTSOC/SOCT	S13	24-Lead (300-Mil) Molded SOIC	
7.0	CY54FCT480BTLMB	L64	28-Square Leadless Chip Carrier	Military
7.5	CY74FCT480ATPC	P13/13A	24-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT480ATQCT	Q13	24-Lead (150-Mil) QSOP	

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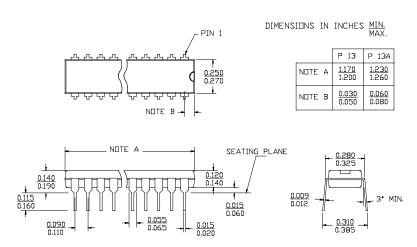


Package Diagrams

28-Square Leadless Chip Carrier L64 MIL-STD-1835 C-4



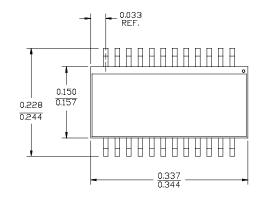
24-Lead (300-Mil) Molded DIP P13/P13A

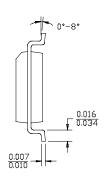


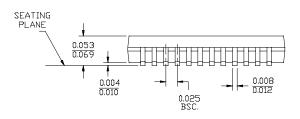


Package Diagrams (continued)

24-Lead Quarter Size Outline Q13

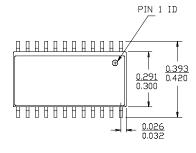




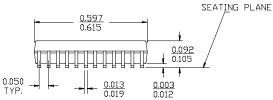


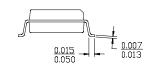
DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.

24-Lead (300-Mil) Molded SOIC S13



DIMENSIONS IN INCHES MIN. MAX.
LEAD COPLANARITY 0.004 MAX.





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